

# MOSFET – N-Channel, POWERTRENCH®

**40 V, 18 A, 26 mΩ**

## FDMC8015L

### General Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

### Features

- Max  $R_{DS(on)}$  = 26 mΩ at  $V_{GS} = 10$  V,  $I_D = 7$  A
- Max  $R_{DS(on)}$  = 36 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 6$  A
- Low Profile – 1 mm Max in Power 33
- 100% UIL Tested
- This Device is Pb-Free, Halide Free and is RoHS Compliant

### Applications

- Load Switch
- Motor Bridge Switch

### MOSFET MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

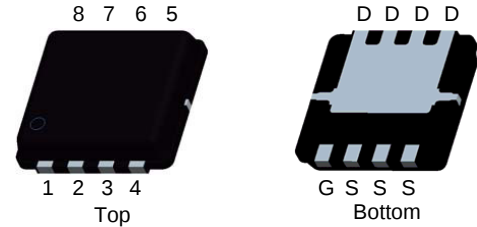
| Symbol         | Parameter                                                                                                                                                                                          | Ratings             | Unit             |
|----------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------|------------------|
| $V_{DS}$       | Drain to Source Voltage                                                                                                                                                                            | 40                  | V                |
| $V_{GS}$       | Gate to Source Voltage                                                                                                                                                                             | $\pm 20$            | V                |
| $I_D$          | Drain Current<br>– Continuous (Package Limited) $T_C = 25^\circ\text{C}$<br>– Continuous (Silicon Limited) $T_C = 25^\circ\text{C}$<br>– Continuous $T_A = 25^\circ\text{C}$ (Note 1a)<br>– Pulsed | 18<br>22<br>7<br>30 | A                |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 3)                                                                                                                                                             | 32                  | mJ               |
| $P_D$          | Power Dissipation<br>$T_C = 25^\circ\text{C}$<br>$T_A = 25^\circ\text{C}$ (Note 1a)                                                                                                                | 24<br>2.3           | W                |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range                                                                                                                                                   | $-55$ to $+150$     | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

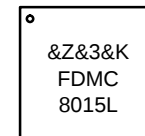
| Symbol          | Parameter                                         | Ratings | Unit                      |
|-----------------|---------------------------------------------------|---------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case              | 5.1     | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 53      |                           |

| $V_{DS}$ | $R_{DS(on)}$ MAX | $I_D$ MAX |
|----------|------------------|-----------|
| 40 V     | 26 mΩ @ 10 V     | 18 A      |
|          | 36 mΩ @ 4.5 V    |           |



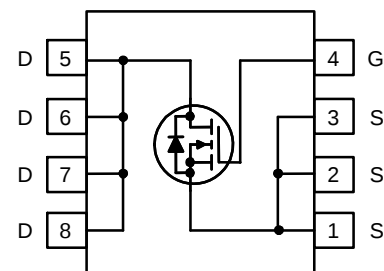
WDFN8 3.3x3.3, 0.65P  
CASE 511DR

### MARKING DIAGRAM



&Z = Assembly Plant Code  
&3 = 3-Digit Date Code  
&K = 2-Digits Lot Run Traceability Code  
FDMC8015L = Device Code

### PIN ASSIGNMENT



### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# FDMC8015L

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Typ | Max | Unit |
|--------|-----------|----------------|-----|-----|-----|------|
|--------|-----------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                      |                                           |                                                |    |    |      |       |
|--------------------------------------|-------------------------------------------|------------------------------------------------|----|----|------|-------|
| BV <sub>DSS</sub>                    | Drain to Source Breakdown Voltage         | I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V | 40 | –  | –    | V     |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | I <sub>D</sub> = 250 μA, referenced to 25°C    | –  | 36 | –    | mV/°C |
| I <sub>DSS</sub>                     | Zero Gate Voltage Drain Current           | V <sub>DS</sub> = 32 V, V <sub>GS</sub> = 0 V  | –  | –  | 1    | μA    |
| I <sub>GSS</sub>                     | Gate to Source Leakage Current            | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V | –  | –  | ±100 | nA    |

### ON CHARACTERISTICS

|                                        |                                                          |                                                                      |   |      |    |       |
|----------------------------------------|----------------------------------------------------------|----------------------------------------------------------------------|---|------|----|-------|
| V <sub>GS(th)</sub>                    | Gate to Source Threshold Voltage                         | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA          | 1 | 1.8  | 3  | V     |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | I <sub>D</sub> = 250 μA, referenced to 25°C                          | – | –6   | –  | mV/°C |
| R <sub>DS(on)</sub>                    | Static Drain to Source On Resistance                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7 A                         | – | 19.7 | 26 | mΩ    |
|                                        |                                                          | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 6 A                        | – | 24   | 36 | mΩ    |
|                                        |                                                          | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7 A, T <sub>J</sub> = 125°C | – | 29   | 39 | mΩ    |
| g <sub>FS</sub>                        | Forward Transconductance                                 | V <sub>DD</sub> = 5 V, I <sub>D</sub> = 7 A                          | – | 30   | –  | S     |

### DYNAMIC CHARACTERISTICS

|                  |                              |                                                          |   |     |     |    |
|------------------|------------------------------|----------------------------------------------------------|---|-----|-----|----|
| C <sub>iss</sub> | Input Capacitance            | V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz | – | 710 | 945 | pF |
| C <sub>oss</sub> | Output Capacitance           |                                                          | – | 94  | 125 | pF |
| C <sub>rss</sub> | Reverse Transfer Capacitance |                                                          | – | 58  | 90  | pF |
| R <sub>g</sub>   | Gate Resistance              |                                                          | – | 1.2 | –   | Ω  |

### SWITCHING CHARACTERISTICS

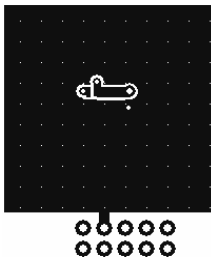
|                     |                               |                                                                                              |   |      |    |    |
|---------------------|-------------------------------|----------------------------------------------------------------------------------------------|---|------|----|----|
| t <sub>d(on)</sub>  | Turn-On Delay Time            | V <sub>DD</sub> = 20 V, I <sub>D</sub> = 7 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω | – | 6.3  | 13 | ns |
| t <sub>r</sub>      | Rise Time                     |                                                                                              | – | 1.9  | 10 | ns |
| t <sub>d(off)</sub> | Turn-Off Delay Time           |                                                                                              | – | 18   | 33 | ns |
| t <sub>f</sub>      | Fall Time                     |                                                                                              | – | 1.7  | 10 | ns |
| Q <sub>g(TOT)</sub> | Total Gate Charge             | V <sub>GS</sub> = 0 V to 10 V, V <sub>DD</sub> = 20 V, I <sub>D</sub> = 7 A                  | – | 13.6 | 19 | nC |
| Q <sub>g(TOT)</sub> | Total Gate Charge             | V <sub>GS</sub> = 0 V to 4.5 V, V <sub>DD</sub> = 20 V, I <sub>D</sub> = 7 A                 | – | 6.6  | 10 | nC |
| Q <sub>gs</sub>     | Gate to Source Charge         | V <sub>DD</sub> = 20 V, I <sub>D</sub> = 7 A                                                 | – | 1.9  | –  | nC |
| Q <sub>gd</sub>     | Gate to Drain "Miller" Charge | V <sub>DD</sub> = 20 V, I <sub>D</sub> = 7 A                                                 | – | 2.5  | –  | nC |

### DRAIN-SOURCE CHARACTERISTICS

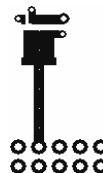
|                 |                                       |                                                      |   |      |     |    |
|-----------------|---------------------------------------|------------------------------------------------------|---|------|-----|----|
| V <sub>SD</sub> | Source to Drain Diode Forward Voltage | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 7 A (Note 2) | – | 0.84 | 1.2 | V  |
|                 |                                       | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2 A (Note 2) | – | 0.76 | 1.1 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                 | I <sub>F</sub> = 7 A, di/dt = 100 A/μs               | – | 18   | 33  | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge               |                                                      | – | 8.6  | 18  | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. R<sub>θJA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.



a. 53°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 125°C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T<sub>J</sub> = 25°C; N-ch: L = 1 mH, I<sub>AS</sub> = 8 A, V<sub>DD</sub> = 36 V, V<sub>GS</sub> = 10 V.

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

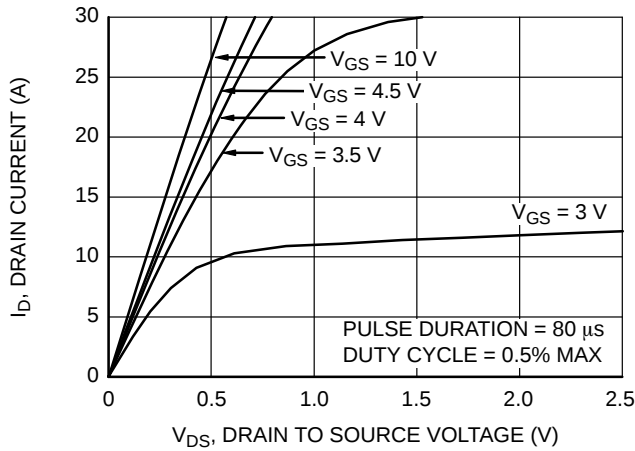


Figure 1. On Region Characteristics

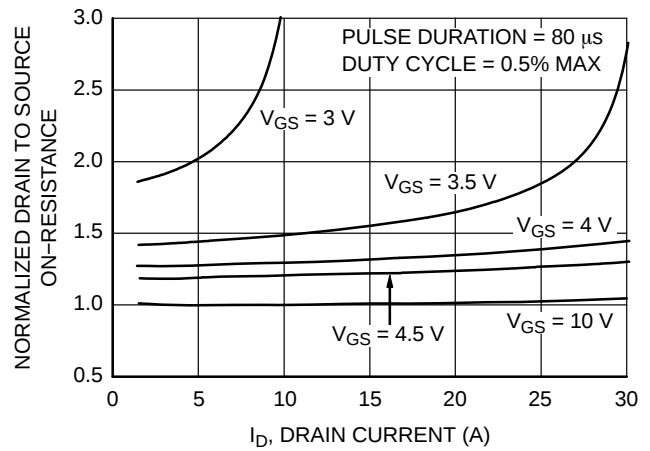


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

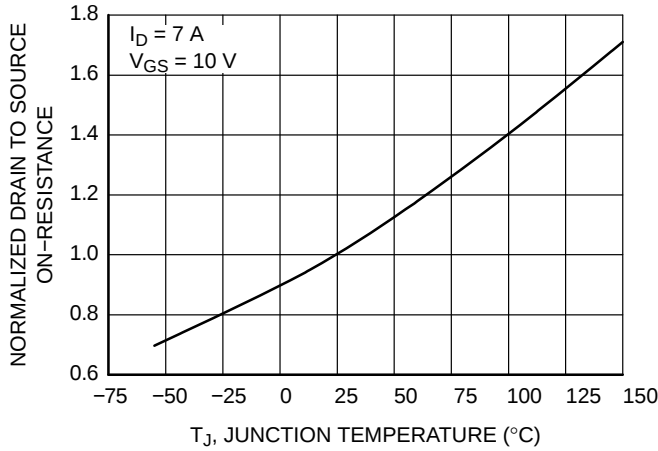


Figure 3. Normalized On Resistance vs. Junction Temperature

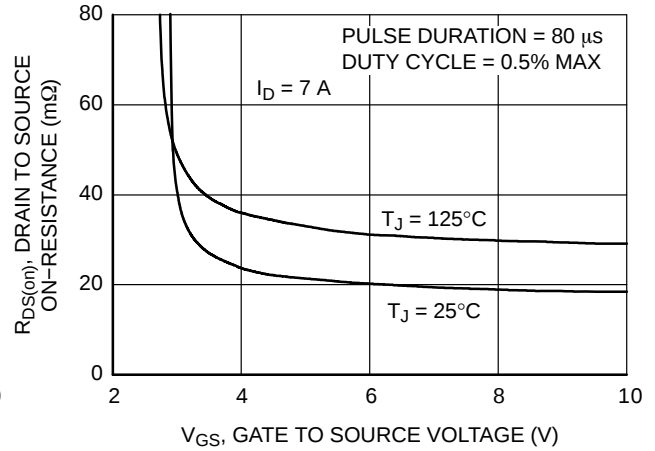


Figure 4. On-Resistance vs. Gate to Source Voltage

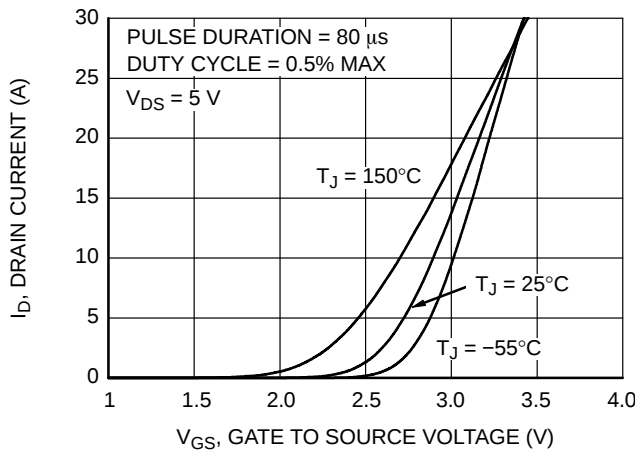


Figure 5. Transfer Characteristics

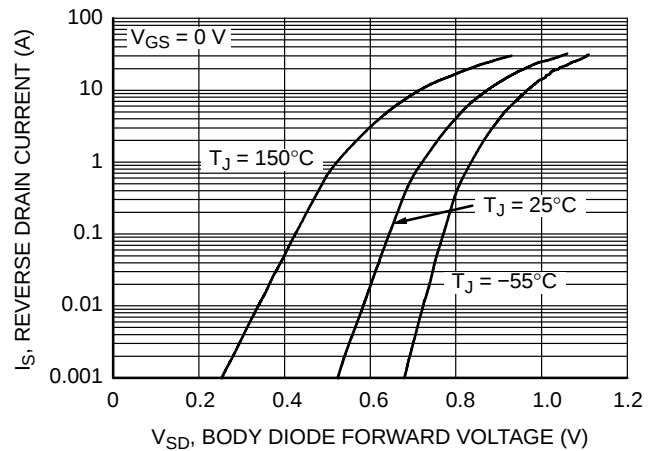


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise noted) (continued)

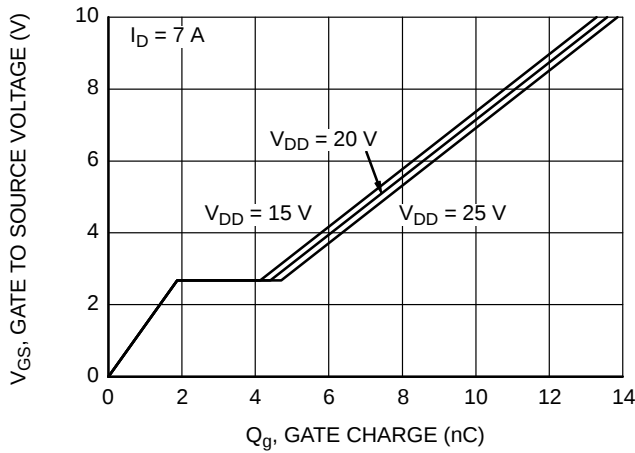


Figure 7. Gate Charge Characteristics

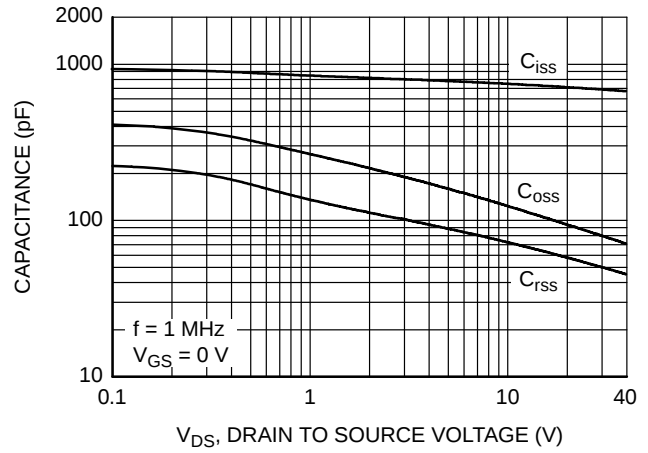


Figure 8. Capacitance vs. Drain to Source Voltage

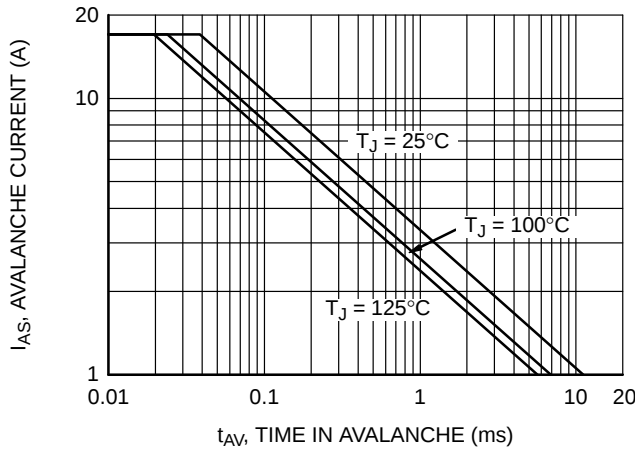


Figure 9. Unclamped Inductive Switching Capability

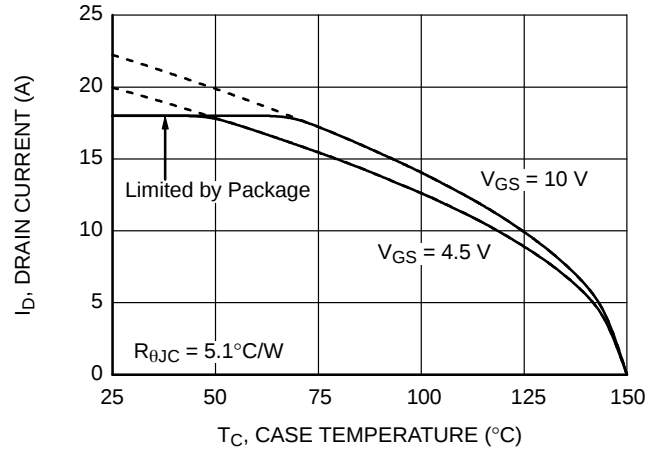


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

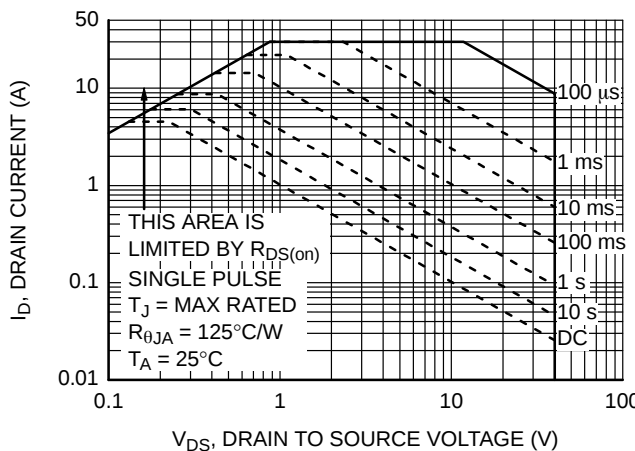


Figure 11. Forward Bias Safe Operating Area

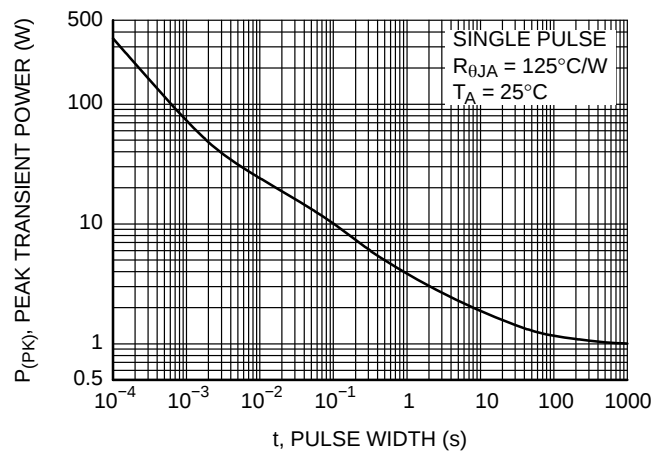


Figure 12. Single Pulse Maximum Power Dissipation

# FDMC8015L

## TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , unless otherwise noted) (continued)

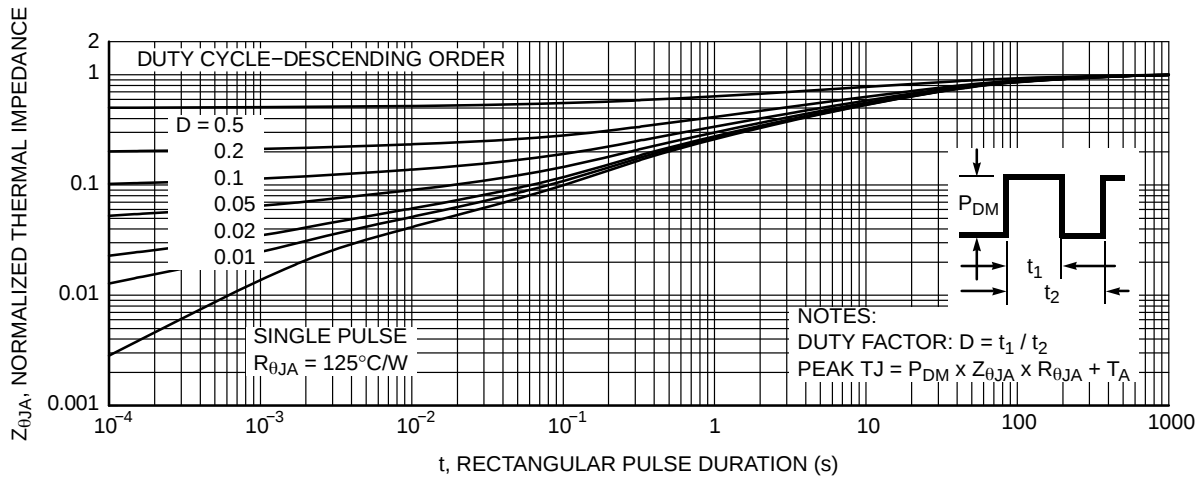
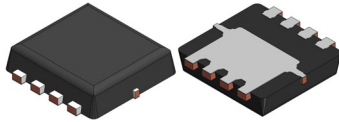


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

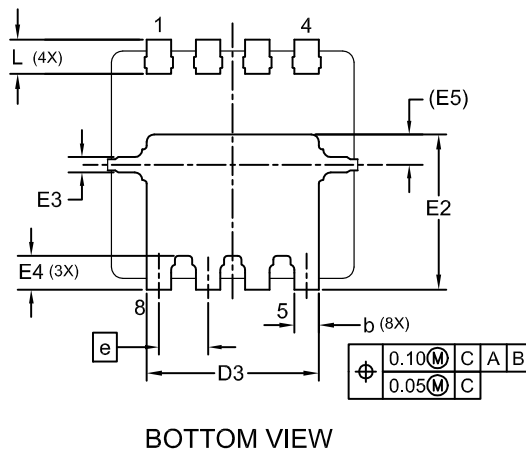
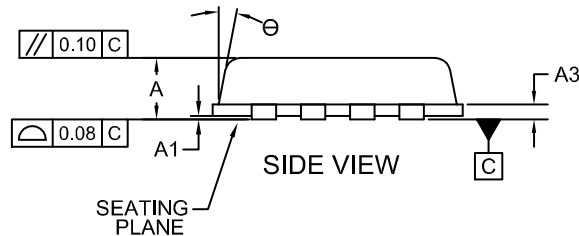
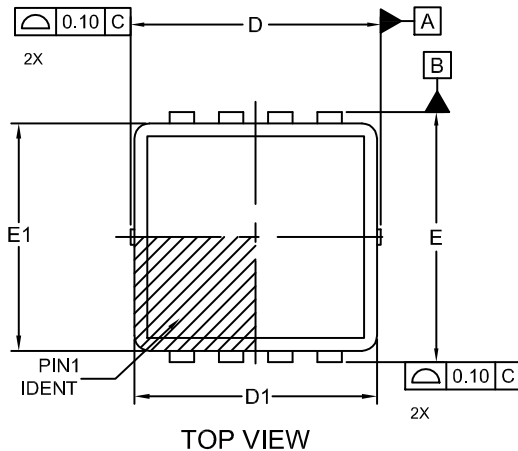
### PACKAGE MARKING AND ORDERING INFORMATION

| Device    | Device Marking | Package                                        | Reel Size | Tape Width | Shipping <sup>†</sup> |
|-----------|----------------|------------------------------------------------|-----------|------------|-----------------------|
| FDMC8015L | FDMC8015L      | WDFN8 3.3x3.3, 0.65P<br>(Pb-Free, Halide Free) | 13"       | 12 mm      | 3000 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

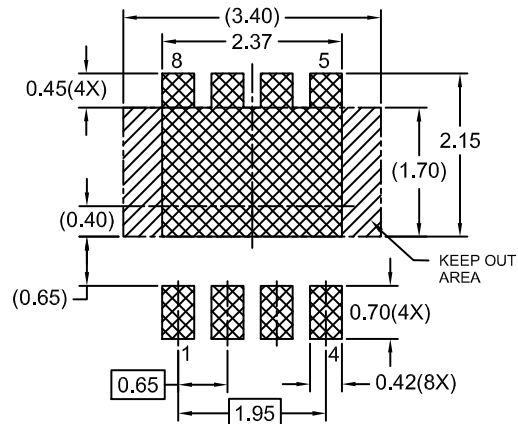

**WDFN8 3.3x3.3, 0.65P**  
**CASE 511DR**  
**ISSUE B**

DATE 02 FEB 2022

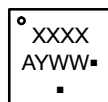

**NOTES:**

- A. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.  
B. SEATING PLANE IS DEFINED BY TERMINAL TIPS ONLY  
C. BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS. MOLD FLASH PROTRUSION OR GATE BURR DOES NOT EXCEED 0.150MM.

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN         | NOM  | MAX  |
| A   | 0.70        | 0.75 | 0.80 |
| A1  | 0.00        | -    | 0.05 |
| A3  | 0.15        | 0.20 | 0.25 |
| b   | 0.27        | 0.32 | 0.37 |
| D   | 3.20        | 3.30 | 3.40 |
| D1  | 3.10        | 3.20 | 3.30 |
| D3  | 2.17        | 2.27 | 2.37 |
| E   | 3.20        | 3.30 | 3.40 |
| E1  | 2.90        | 3.00 | 3.10 |
| E2  | 1.95        | 2.05 | 2.15 |
| E3  | 0.15        | 0.20 | 0.25 |
| E4  | 0.30        | 0.40 | 0.50 |
| E5  | 0.40 REF    |      |      |
| e   | 0.65 BSC    |      |      |
| L   | 0.30        | 0.40 | 0.50 |
| Θ   | 0°          | -    | 12°  |


**RECOMMENDED LAND PATTERN**

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM\***


XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

|                         |                             |                                                                                                                                                                                     |
|-------------------------|-----------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| <b>DESCRIPTION:</b>     | <b>WDFN8 3.3x3.3, 0.65P</b> | <b>PAGE 1 OF 1</b>                                                                                                                                                                  |

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